



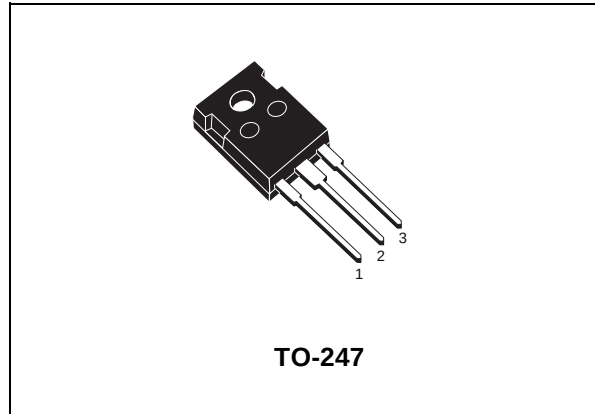
STGW30NB60HD

N-CHANNEL 30A - 600V - TO-247

PowerMESH™ IGBT

TYPE	V _{CES}	V _{CE(sat)} (Max)	I _C
STGW30NB60HD	600 V	< 2.8 V	30 A

- HIGH INPUT IMPEDANCE (VOLTAGE DRIVEN)
- LOW ON-VOLTAGE DROP (V_{CESAT})
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- VERY HIGH FREQUENCY OPERATION
- OFF LOSSES INCLUDE TAIL CURRENT
- CO-PACKAGED WITH TORBOSWITCH™ ANTIPARALLEL DIODE

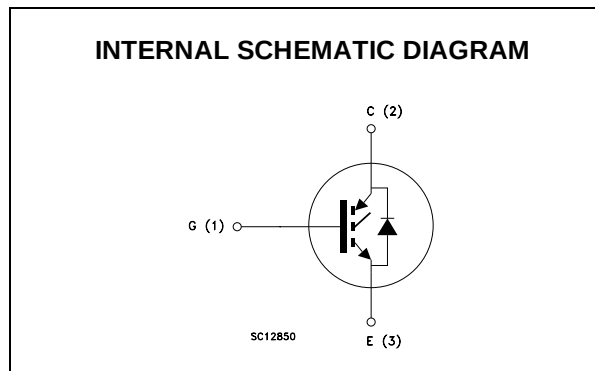


DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "H" identifies a family optimized to achieve very low switching times for high frequency applications (<120KHz).

APPLICATIONS

- HIGH FREQUENCY MOTOR CONTROLS
- WELDING EQUIPMENTS
- SMPS AND PFC IN BOTH HARD SWITCH AND RESONANT TOPOLOGIES



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)	600	V
V _{ECR}	Emitter-Collector Voltage	20	V
V _{GE}	Gate-Emitter Voltage	± 20	V
I _C	Collector Current (continuous) at T _C = 25°C	60	A
I _C	Collector Current (continuous) at T _C = 100°C	30	A
I _{CM} (■)	Collector Current (pulsed)	240	A
P _{TOT}	Total Dissipation at T _C = 25°C	190	W
	Derating Factor	1.52	W/°C
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

Note: NEW DATASHEET ACCORDING TO PCN DSG/CT/XXXX
March 2003

(●) Pulse width limited by safe operating area

STGW30NB60HD

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	0.66	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	30	°C/W
Rthc-h	Thermal Resistance Case-heatsink Typ	0.1	°C/W

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{BR(CES)}	Collectro-Emitter Breakdown Voltage	I _C = 250 µA, V _{GE} = 0	600			V
I _{CES}	Collector cut-off (V _{GE} = 0)	V _{CE} = Max Rating, T _C = 25 °C V _{CE} = Max Rating, T _C = 125 °C			100 1000	µA µA
I _{GES}	Gate-Emitter Leakage Current (V _{CE} = 0)	V _{GE} = ± 20 V, V _{CE} = 0			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GE(th)}	Gate Threshold Voltage	V _{CE} = V _{GE} , I _C = 250 µA	3		5	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} =15 V, I _C =30 A V _{GE} =15 V, I _C =30 A, T _C =125°C		2.2 1.8	2.8	V V

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs}	Forward Transconductance	V _{CE} = 25 V, I _C = 30 A		20		S
C _{ies}	Input Capacitance	V _{CE} = 25 V, f = 1 MHz, V _{GE} = 0		2300		pF
C _{oes}	Output Capacitance			250		pF
C _{res}	Reverse Transfer Capacitance			72		pF
Q _g Q _{ge} Q _{gc}	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	V _{CE} = 480 V, I _C = 30 A, V _{GE} = 15 V		150 15 72	210	nC nC nC
I _{CL}	Latching Current	V _{clamp} = 480 V, R _G = 10 Ω V _{GE} = 15 V, T _J = 150°C	120			A

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t _{d(on)} t _r	Delay Time Rise Time	V _{CC} = 480 V, I _C = 30 A V _{GE} = 15 V, R _G = 10Ω		15 35		ns ns
(di/dt) _{on} E _{on}	Turn-on Current Slope Turn-on Switching Losses	V _{CC} = 480 V, I _C = 30 A, R _G =10 Ω V _{GE} = 15 V, T _J = 125°C		1000 1000		A/µs µJ

ELECTRICAL CHARACTERISTICS (CONTINUED)**SWITCHING OFF**

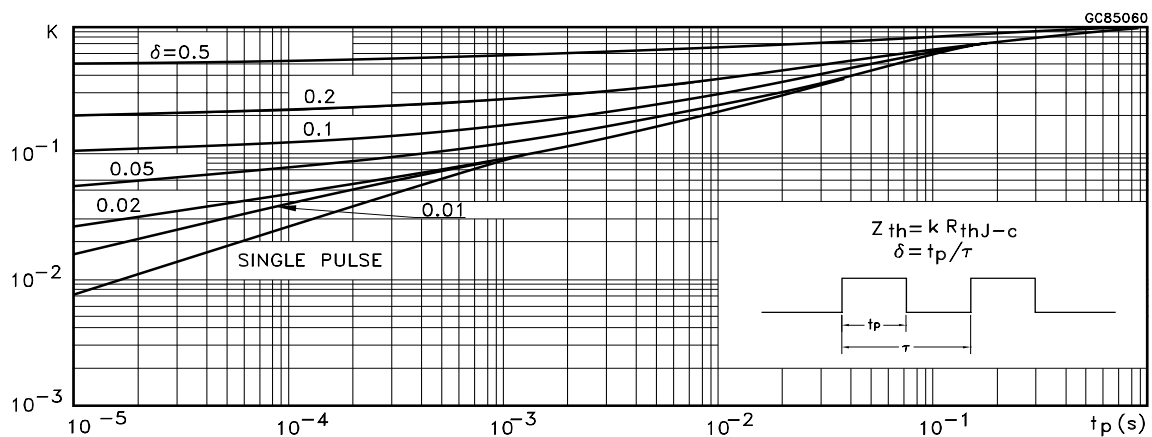
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_c	Cross-over Time	$V_{CC} = 480 \text{ V}$, $I_C = 30 \text{ A}$, $R_{GE} = 10 \Omega$, $V_{GE} = 15 \text{ V}$		150		ns
$t_r(V_{off})$	Off Voltage Rise Time			40		ns
$t_d(off)$	Delay Time			210		ns
t_f	Fall Time			90		ns
$E_{off}(^{**})$	Turn-off Switching Loss			1.10		mJ
E_{TS}	Total Switching Loss			2.0		mJ
t_c	Cross-over Time	$V_{CC} = 480 \text{ V}$, $I_C = 30 \text{ A}$, $R_{GE} = 10 \Omega$, $V_{GE} = 15 \text{ V}$ $T_j = 125^\circ \text{C}$		250		ns
$t_r(V_{off})$	Off Voltage Rise Time			70		ns
$t_d(off)$	Delay Time			250		ns
t_f	Fall Time			160		ns
$E_{off}(^{**})$	Turn-off Switching Loss			1.6		mJ
E_{TS}	Total Switching Loss			2.65		mJ

Note: (*)Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

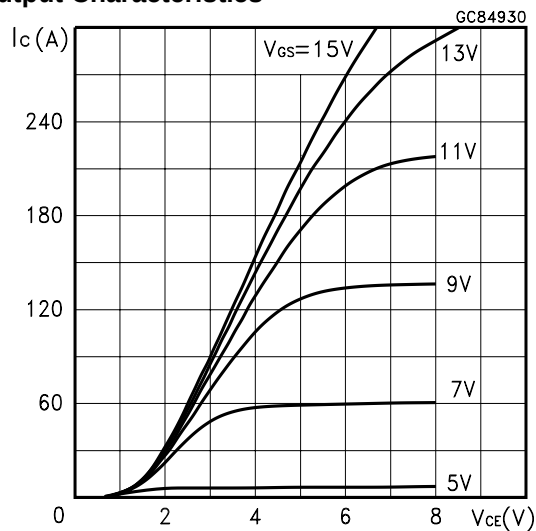
(**)Losses include Also the Tail (Jedec Standardization)

COLLECTOR-EMITTER DIODE

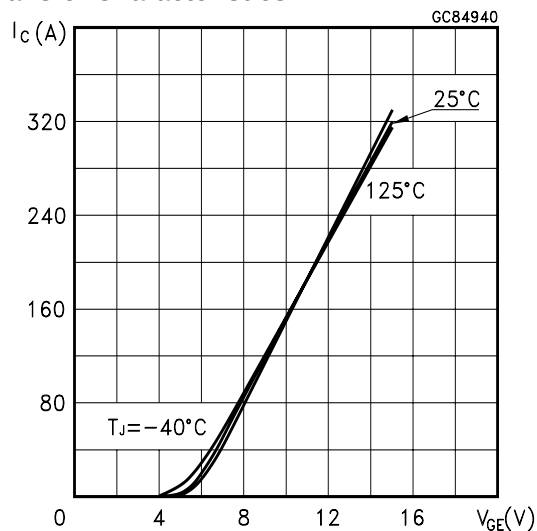
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_f	Forward Current				15	A
I_{fm}	Forward Current pulsed				120	A
V_f	Forward On-Voltage	$I_f = 15 \text{ A}$		1.4	2.0	V
		$I_f = 15 \text{ A}$, $T_j = 125^\circ \text{C}$		1.25		V
t_{rr}	Reverse Recovery Time	$I_f = 15 \text{ A}$, $V_R = 27 \text{ V}$, $T_j = 125^\circ \text{C}$, $di/dt = 100 \text{ A}/\mu\text{s}$		84		ns
Q_{rr}	Reverse Recovery Charge			201		nC
I_{rrm}	Reverse Recovery Current			4.8		A

Thermal Impedance

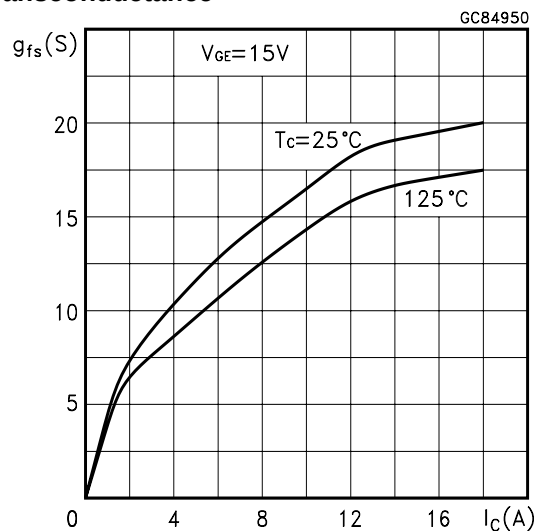
Output Characteristics



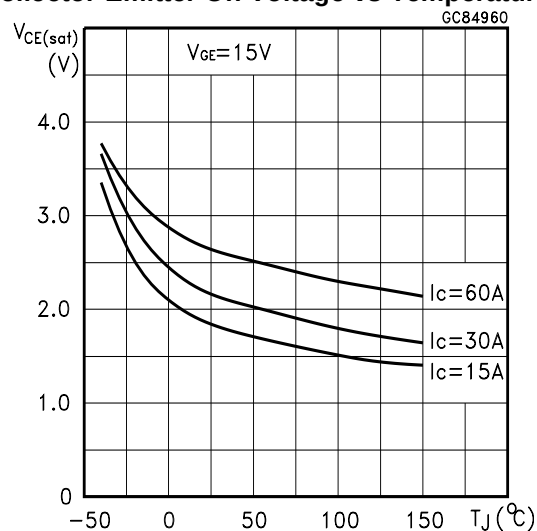
Transfer Characteristics



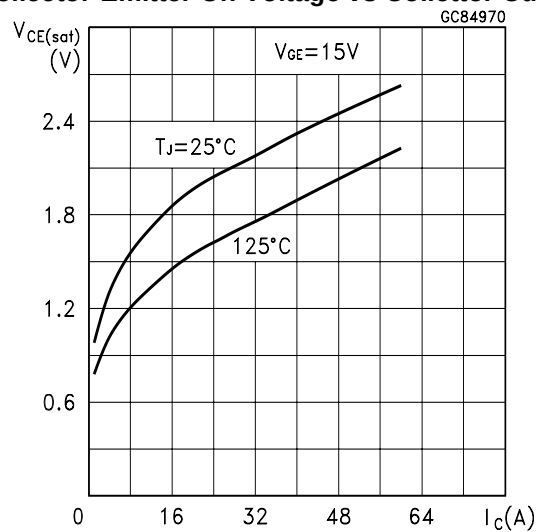
Transconductance



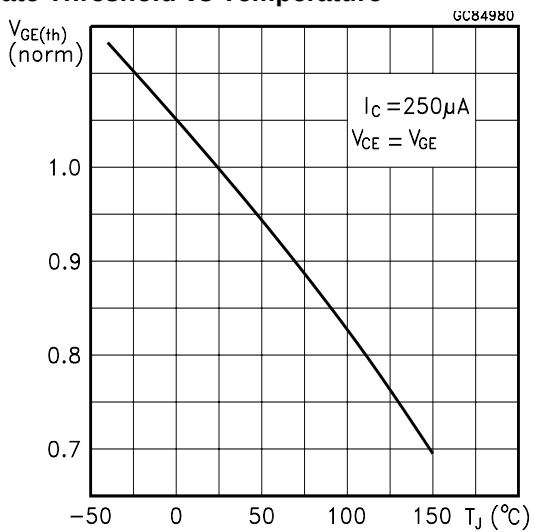
Collector-Emitter On Voltage vs Temperature



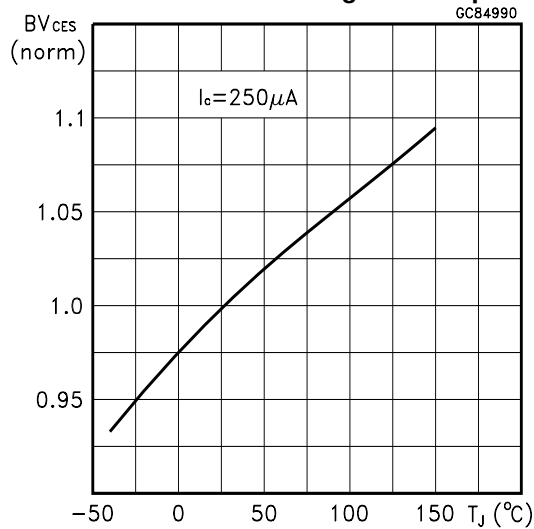
Collector-Emitter On Voltage vs Collector Current



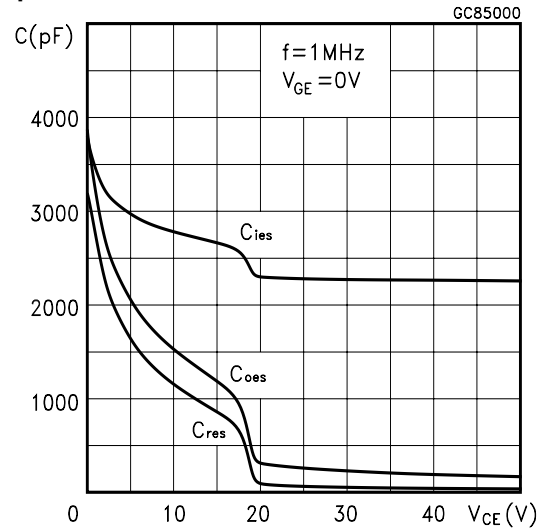
Gate Threshold vs Temperature



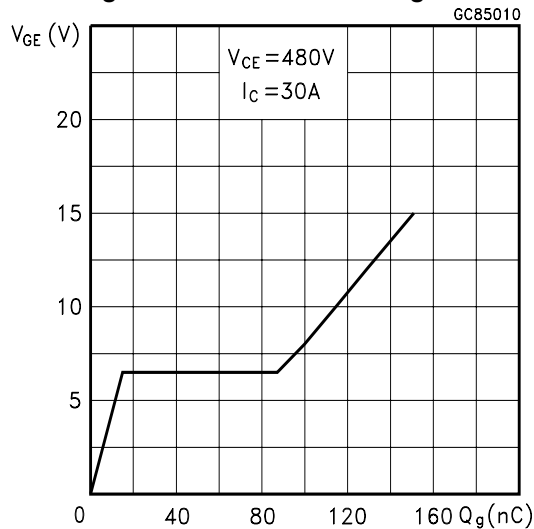
Normalized Breakdown Voltage vs Temperature



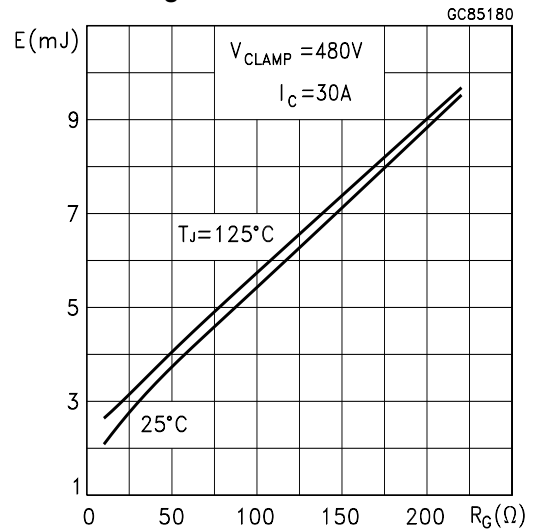
Capacitance Variations



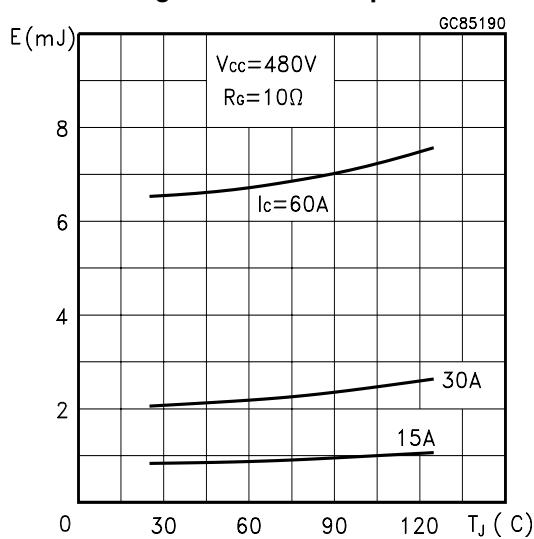
Gate Charge vs Gate-Emitter Voltage



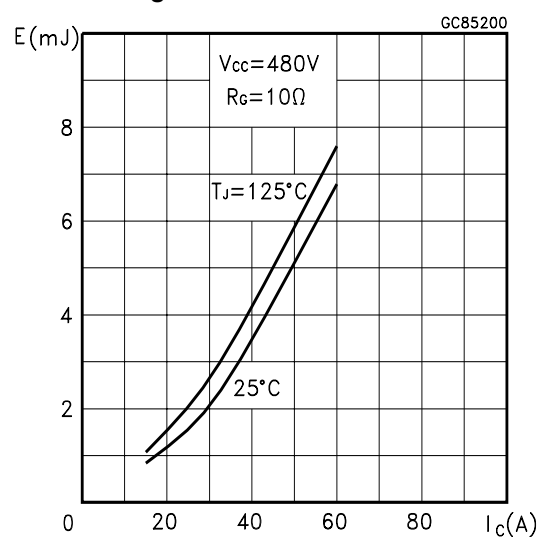
Total Switching Losses vs Gate Resistance



Total Switching Losses vs Temperature



Total Switching Losses vs Collector Current



Switching Off Safe Operating Area

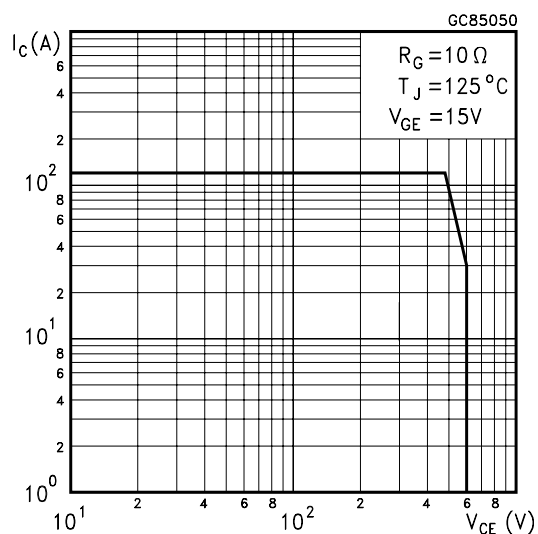
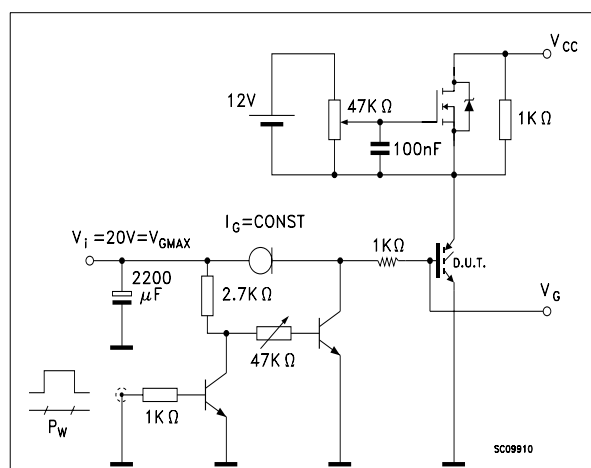


Fig. 1: Gate Charge test Circuit



Diode Forward Voltage

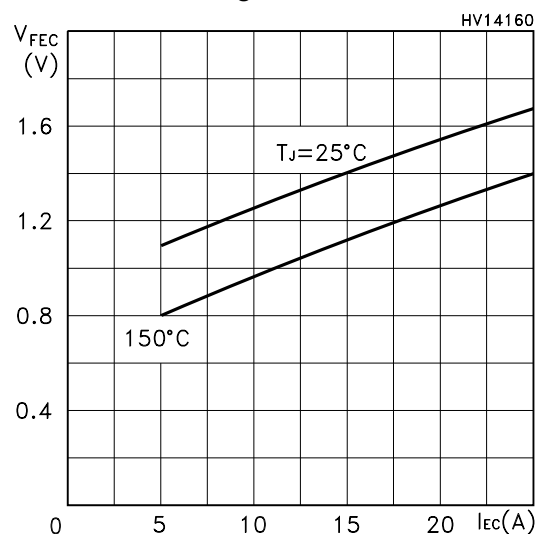
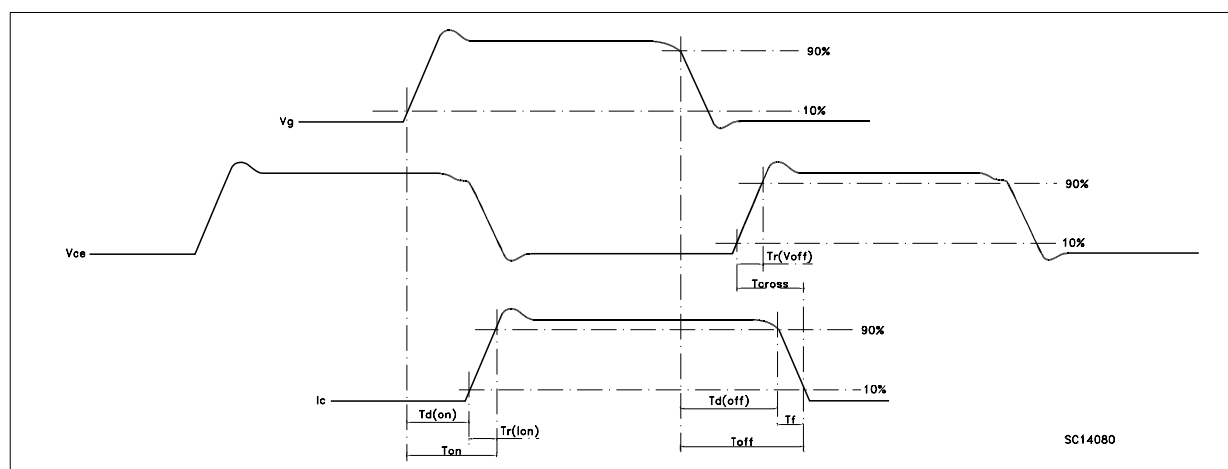
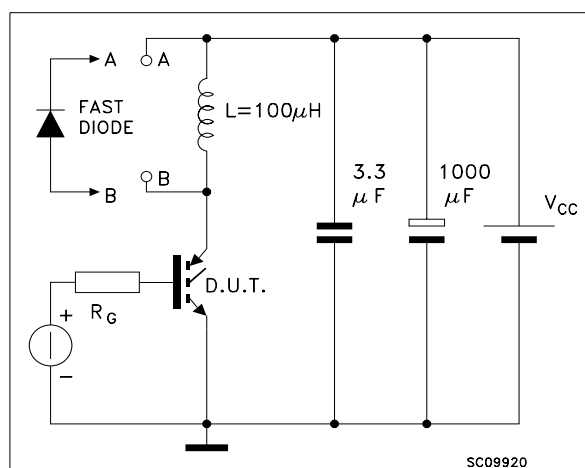
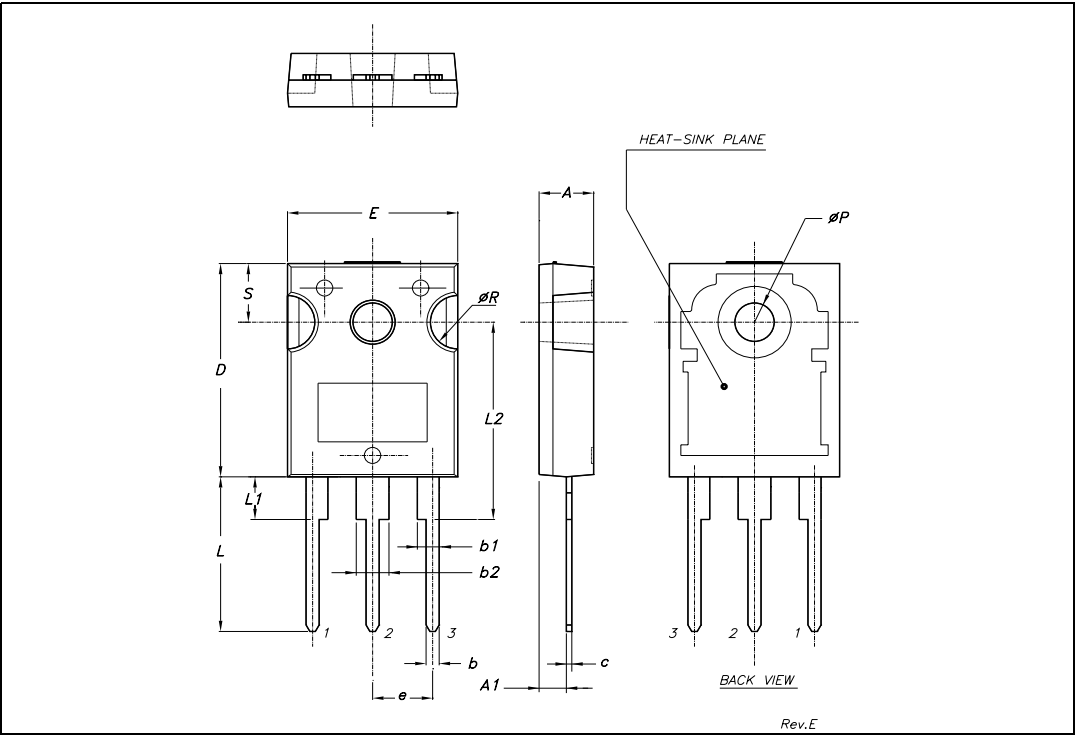


Fig. 2: Test Circuit For Inductive Load Switching



TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.086		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



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